

1N52
GOLD BONDED GERMANIUM DIODE

FEATURES

Low forward voltage drop—low power consumption
 Thirty years of proven reliability—one million hours mean time between failures (MTBF)
 Very low noise level
 Metallurgically bonded

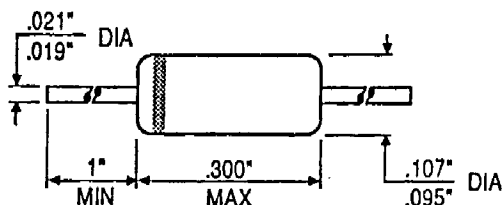
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage 85 Volts
 Peak Forward Current 500 mA
 Operating Temperature Range - 65 °C to 85 °C
 Average Power Dissipation 80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	85		V	25 °C
Reverse Current	I_r	50 V		150	μ A	25 °C
Forward Voltage	V_f	5 mA		1	V	25 °C

MECHANICAL



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

